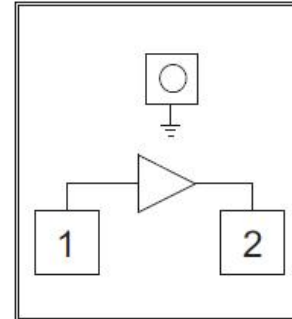


## High Linearity, Low Noise Gain Block chip, 0.1-3GHz

### Performance characteristics

- Working frequency band : 0.1-3GHz
- Noise figure: <1.0dB @100MHz~2GHz
- Small signal gain: 25.5dB@1GHz
- P-1dB: 17dBm Typ
- OIP3: 33 dBm
- 50Ohm input and output
- + 3V / 60mA
- DIE: 0.83 x 0.93 x0.1mm

### Functional Block Diagram



### Use restriction parameter <sup>1</sup>

Collector voltage	+6 V
Input power	+20dBm
Operating Current	80mA
Operating temperature	-55 ~ + 105 °C
Storage temperature	-65 ~ +150°C

【1】 Exceeding any of these maximum limits may cause permanent damage.

### Electrical performance parameters ( TA = +25°C, Vd = +3V, 50Ω system)

Index	Test Conditions	Minimum	Typical Value	Maximum	Unit
Frequency Range		0.1		3	GHz
Test frequency			1		GHz
Small Signal Gain			25.5		dB
Input return loss			12		dB
Output return loss			14		dB
P-1			17.5		dBm
OIP3	Pout = 0 dBm/tone, Δf = 1 MHz		34		dBm
Noise Figure	Without de-embedding, the estimated evaluation board loss is 0.15dB@1.0G		0.65		dB
Current	Static		60		mA

\*The noise figure result does not deduct the input loss of the test DEMO board .

## High Linearity, Low Noise Gain Block chip, 0.1-3GHz

### 0.1-3GHz electrical performance parameters

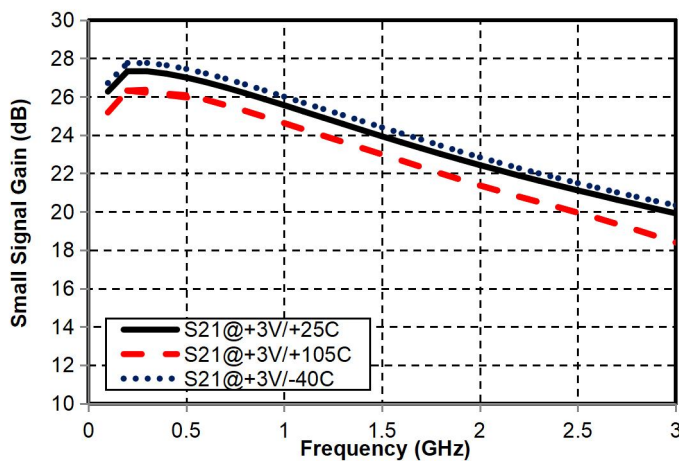
Electrical performance parameters ( TA = +25°C, Vd = +3V, 50Ω system, 60mA )

Index	Typical Value						Unit
	0.1	0.4	0.9	1.9	2.45	3.5	
Test frequency	0.1	0.4	0.9	1.9	2.45	3.5	MHz
Small Signal Gain	26.0	27.0	25.5	22.5	21.0	18.5	dB
Input return loss	6.0	12.0	12.0	12.0	12.0	21.0	dB
Output return loss	7.0	15.0	15.0	9.0	8.0	9.5	dB
P-1	18.0	17.5	17.5	17.5	17.5	16.0	dBm
OIP3*	32.0	36.0	34.0	34.5	33.0	30.5	dBm
Noise Figure**	1.0	0.6	0.7	1.0	1.2	2.2	dB

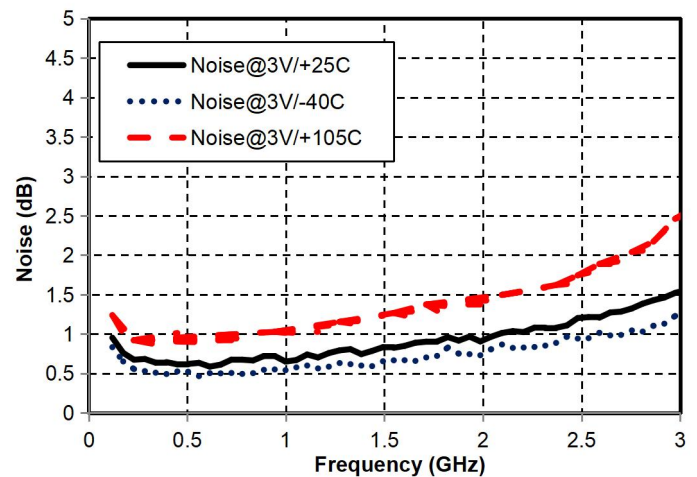
\* Pout=+ 0dBm /tone, Δf =1MHz .

\*\* Noise figure results do not deduct the input loss of the test DEMO board .

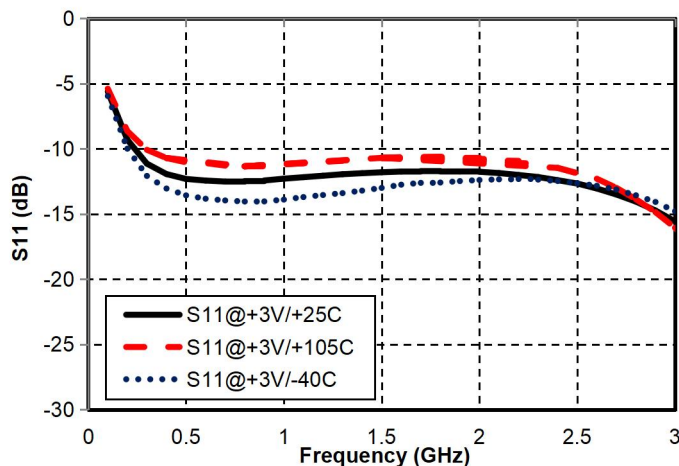
Small Signal Gain vs. Frequency



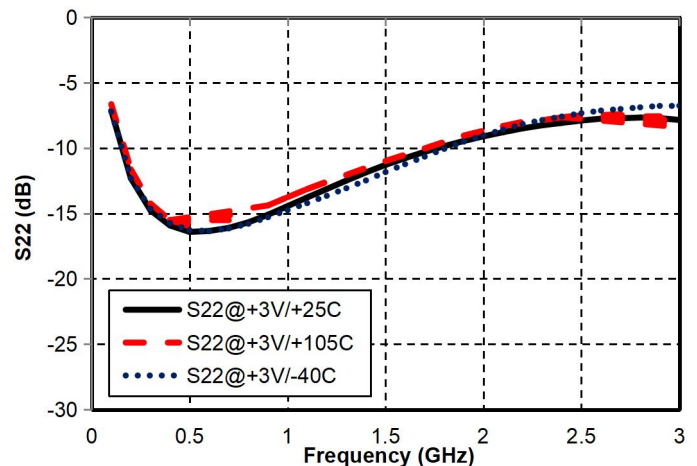
Noise Figure vs. Frequency



Input Return Loss vs. Frequency

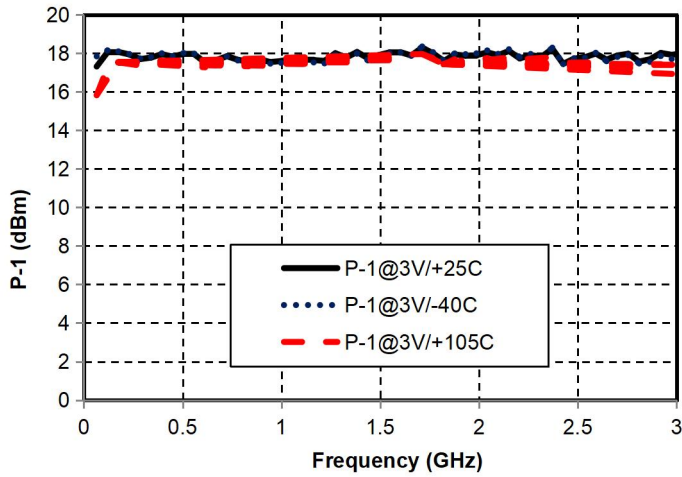


Output Return Loss vs. Frequency

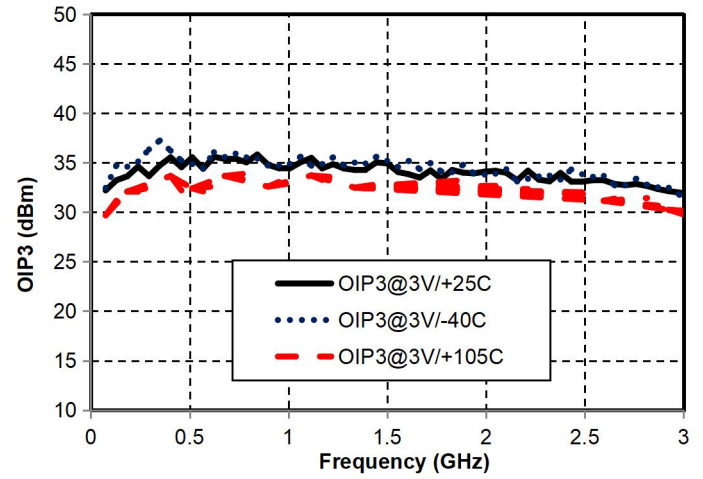


## High Linearity Low Noise Gain Amplifier, 0.1-3GHz

P-1dB vs. Frequency

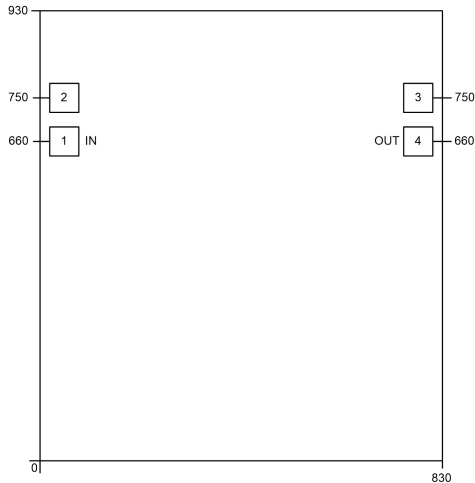


OIP3 vs. Frequency



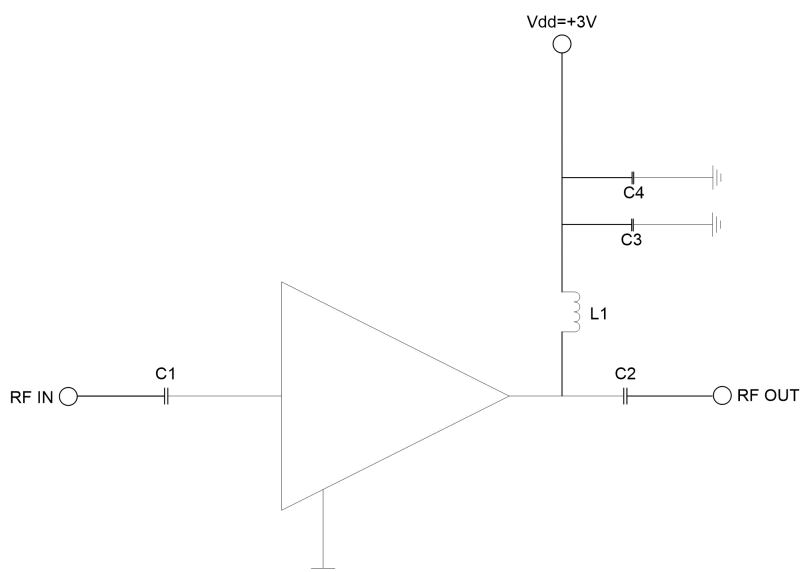
## High Linearity Low Noise Gain Amplifier, 0.1-3GHz

### Appearance structure



Bonding point number	Function Symbol	Functional Description
1	RFIN	RF input, external DC blocking capacitor is required
4	RFOUT	RF output and chip DC bias, bias the circuit at the output end through external choke inductor and bias resistor, and require external DC blocking capacitor
Chip bottom	GND	The bottom of the chip needs to be well grounded to RF and DC

### Recommended circuit diagram



C1 , C2, C3 = 1000pF ; C4 = 1uF; L1 = 82nH ; capacitance and inductance can be adjusted according to different application frequency bands.